

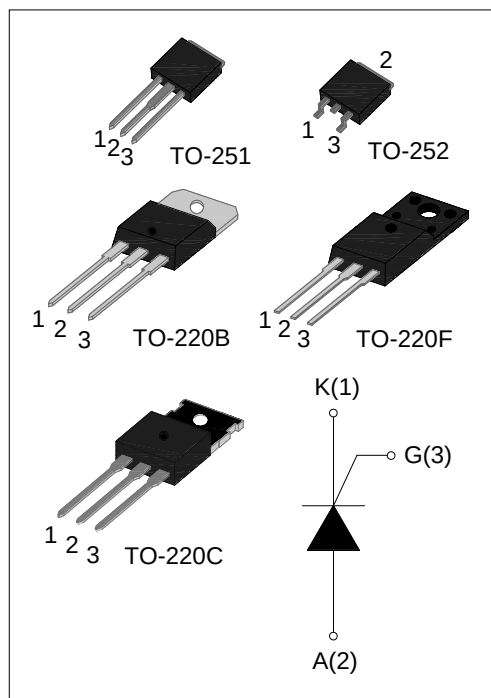


DESCRIPTION:

JCT151 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
I_{GT}	≤ 15	mA
V_{TM}	≤ 1.7	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	$^{\circ}\text{C}$
Operating junction temperature range		T_j	-40 - 125	$^{\circ}\text{C}$
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)		V_{DRM}	650/800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)		V_{RRM}	650/800	V
RMS on-state current	TO-251/ TO-252 ($T_C=98^{\circ}\text{C}$)	$I_{T(RMS)}$	12	A
	TO-220B/ TO-220C ($T_C=100^{\circ}\text{C}$)			
	TO-220F ($T_C=85^{\circ}\text{C}$)			
Non repetitive surge peak on-state current ($t_p=10\text{ms}$)		I_{TSM}	120	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	72	A^2s
Repetitive rate of rise of on-state current ($I_G=2 \times I_{GT}$)		dI_T/dt	50	$\text{A}/\mu\text{s}$
Peak gate current		I_{GM}	2	A
Peak gate power		P_{GM}	5	W

Average gate power dissipation	$P_{G(AV)}$	0.5	W
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ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	4	15	mA
V_{GT}		-	0.75	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C } R_L=3.3\text{K}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	12	40	mA
I_H	$I_T=500\text{mA}$	-	12	30	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$	200	400	-	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=23\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.7	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	10	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	1	mA

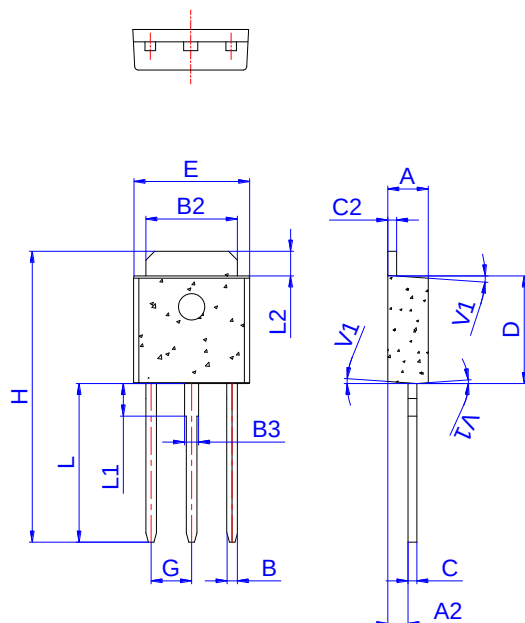
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	TO-251/ TO-252	2.0	$^{\circ}\text{C/W}$
		TO-220B/TO-220C	1.7	
		TO-220F	4.5	

ORDERING INFORMATION

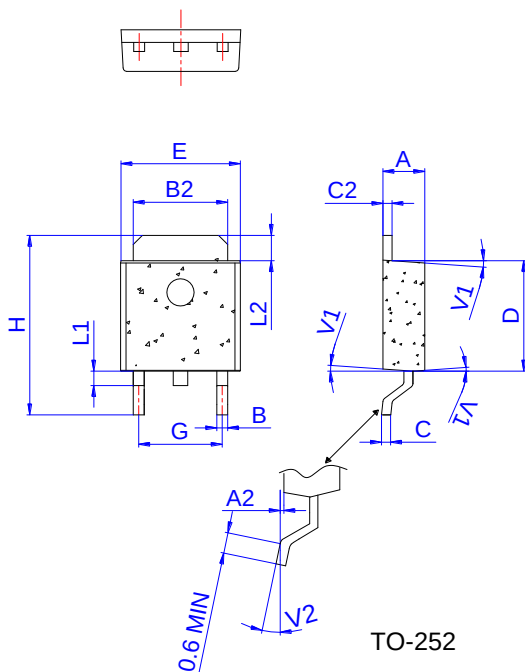
JieJie Microelectronics Co.,Ltd	J	CT	151	B	-650R
	SCRs		$I_T(\text{RMS}):12\text{A}$	650R: $V_{DRM}/V_{RRM} \geq 650\text{V}$ 800R: $V_{DRM}/V_{RRM} \geq 800\text{V}$ F:TO-220F H:TO-251K:TO-252 B:TO-220B C:TO-220C	

PACKAGE MECHANICAL DATA



TO-251

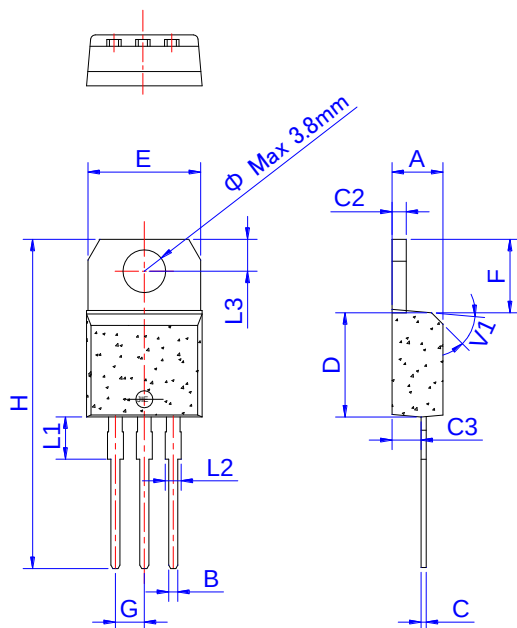
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



TO-252

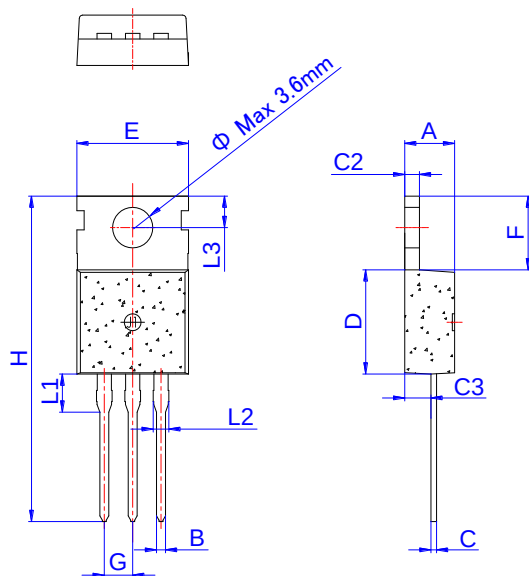
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA



TO-220B

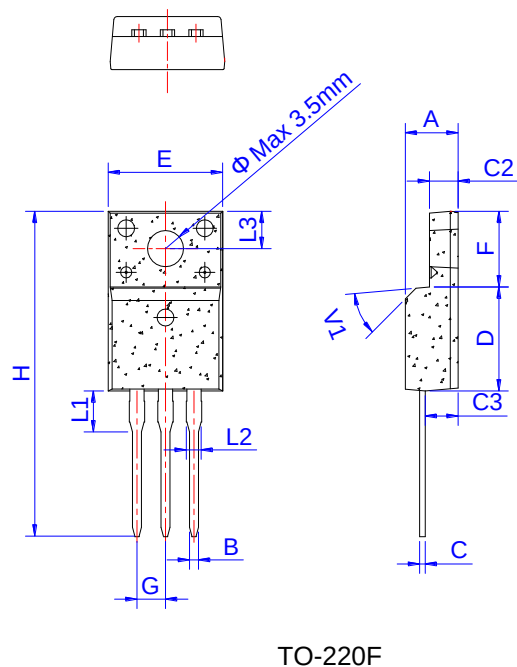
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

FIG.1: Maximum power dissipation versus RMS on-state current

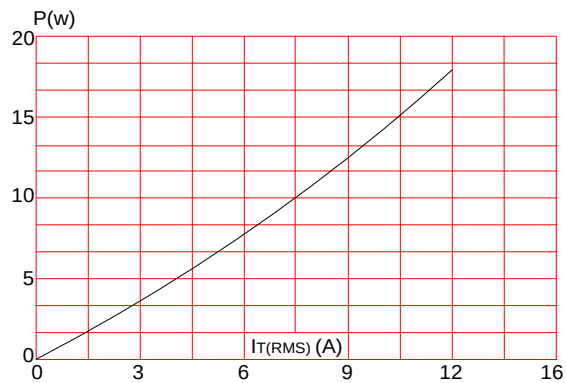


FIG.2: RMS on-state current versus case temperature

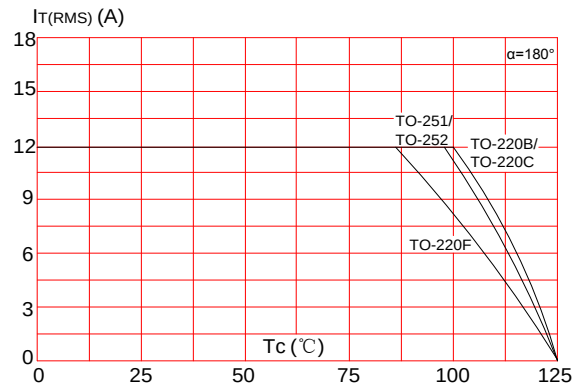


FIG.3: Surge peak on-state current versus number of cycles

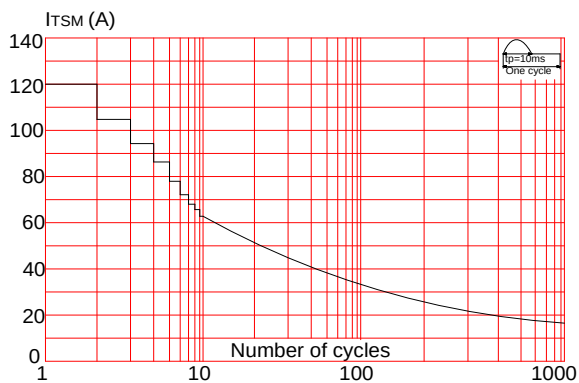


FIG.4: On-state characteristics (maximum values)

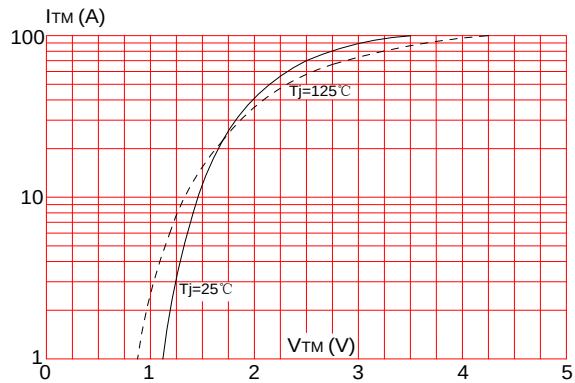


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

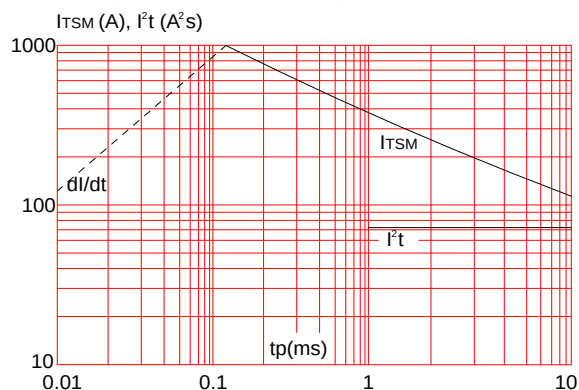
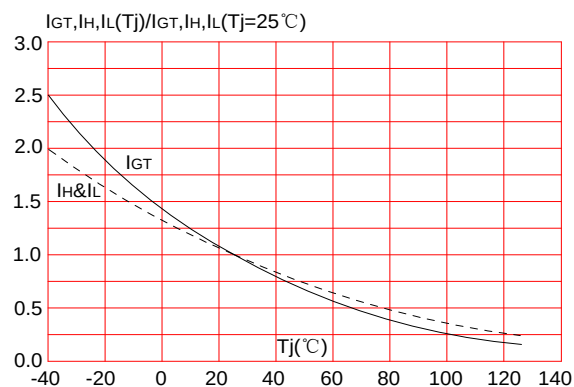


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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